CLIPPEDIMAGE= JP363213965A
PAT-NO: JP363213965A
DOCUMENT-IDENTIFIER: JP 63213965 A
TITLE: SEMICONDUCTOR DEVICE

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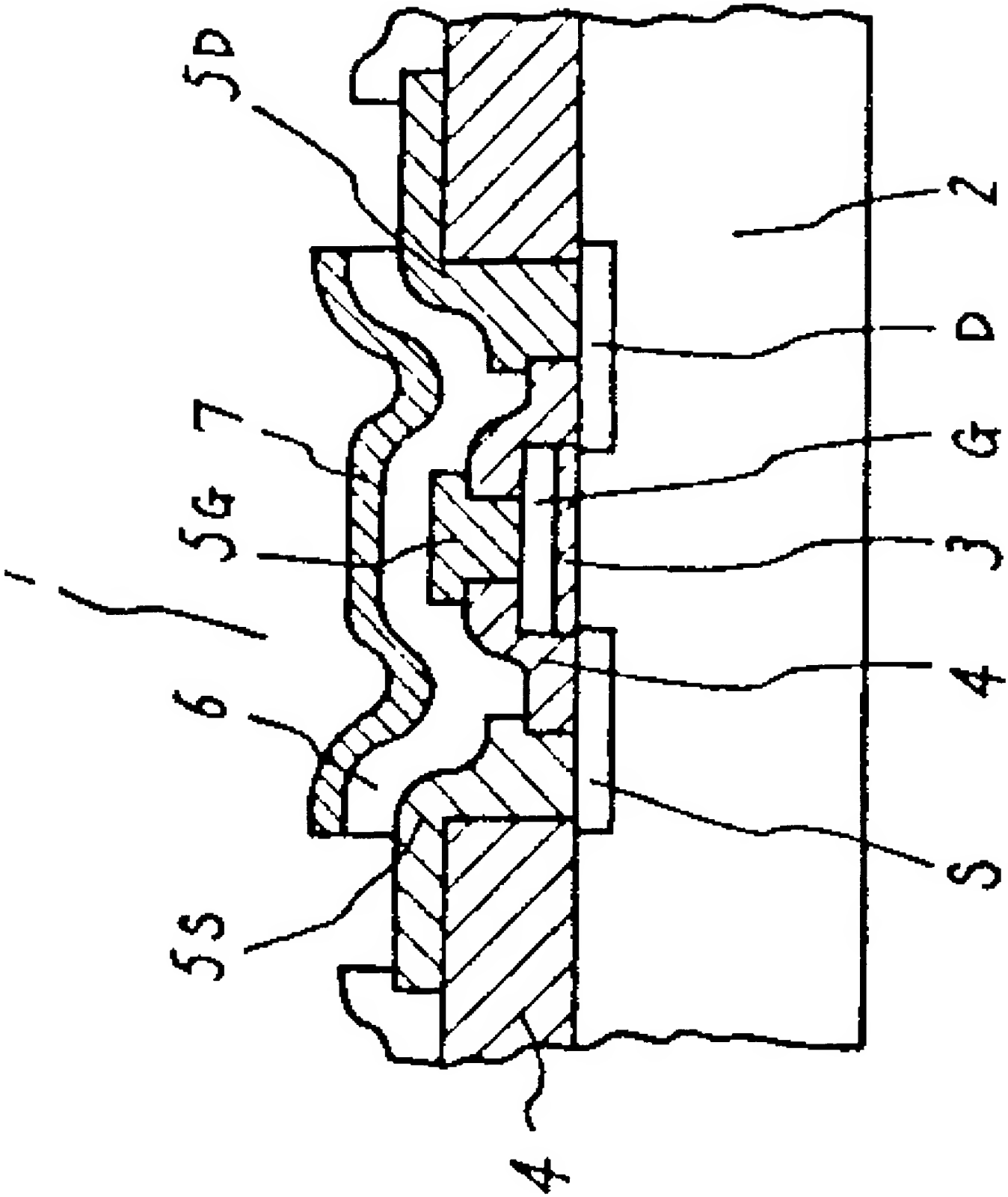
US-CL-CURRENT: 257/296,257/368

ABSTRACT:
PURPOSE: To facilitate a burn-in test, and to reduce cost by forming at least an insulating layer onto a gate electrode for a MOS transistor while shaping a conductive layer, which is arranged oppositely to at least the gate electrode and to which voltage is applied, onto the insulating layer.

CONSTITUTION: An insulating layer 6 has opening sections from which each partial surface of respective wiring layer 5G, 5S, 5D is exposed, and consists of a surface protective film coating separate electrode 5G, 5S, 5D and the upper surface of an inter-layer film 4. The layer 6 is shaped by an silicon oxide film or an silicon nitride film through a CVD method. A conductive layer 7 is positioned to the upper surface of the insulating layer 6 in the upper section of a gate electrode G, and formed by an aluminum film, etc. through a sputtering method in said region in which at least the gate electrode G is shaped. An electrode, which is formed by the same material as the conductive layer 7 and connected electrically and can be connected electrically to external terminals, is disposed, and high voltage is applied on a burn-in. One MOS transistor as a fundamental element is constituted of the gate electrode G,

a source electrode S and a drain electrode D.


5D
2
D
7
G
5G
3
1
4
6
S
5S
4